

RoHS

COMPLIANT HALOGEN

FREE Available

Vishay Siliconix

N-Channel 200-V (D-S) MOSFET

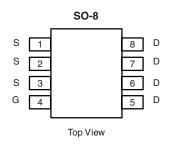
| PRODUCT SUMMARY | | | | |
|---------------------|----------------------------------|--------------------|--|--|
| V _{DS} (V) | R _{DS(on)} (Ω) | I _D (A) | | |
| 200 | 0.240 at V _{GS} = 10 V | 2.2 | | |
| | 0.260 at V _{GS} = 6.0 V | 2.1 | | |

FEATURES

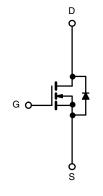
- Halogen-free According to IEC 61249-2-21
 Definition
- TrenchFET[®] Power MOSFET
- PWM Optimized for Low Q_{g} and Low R_{g}
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

Primary Side Switch



Ordering Information: Si4464DY-T1-E3 (Lead (Pb)-free) Si4464DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS $T_A = 25 \text{ °C}$, unless otherwise noted | | | | | | |
|--|-----------------------------------|------------------|-----------|--------------|------|--|
| Parameter | | Symbol | 10 s | Steady State | Unit | |
| Drain-Source Voltage | | V _{DS} | 200 | | V | |
| Gate-Source Voltage | | V _{GS} | ± 20 | | | |
| | T _A = 25 °C | 1- | 2.2 | 1.7 | | |
| Continuous Drain Current (T _J = 150 °C) ^a | T _A = 70 °C | - I _D | 1.7 | 1.3 | ٨ | |
| Pulsed Drain Current | | I _{DM} | 8 | | A | |
| Single Avalanch Current | L = 0.1 mH | I _{AS} | 3 0.45 | | | |
| Single Avalanch Energy | | E _{AS} | | | mJ | |
| Continuous Source Current (Diode Conduction) ^a | | ۱ _S | 2.1 | 1.2 | А | |
| | T _A = 25 °C | 2.5 1.5 | | 1.5 | W | |
| Maximum Power Dissipation ^a | T _A = 70 °C | P _D | 1.6 | 0.9 | VV | |
| Operating Junction and Storage Temperature Rar | T _J , T _{stg} | - 55 to 150 | | °C | | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|--|--------------|-------------------|---------|---------|------|--|
| Parameter | | Symbol | Typical | Maximum | Unit | |
| Maximum lunation to Ambienta | t ≤ 10 s | R _{thJA} | 37 | 50 | | |
| Maximum Junction-to-Ambient ^a | Steady State | | 68 | 85 | °C/W | |
| Maximum Junction-to-Foot (Drain) | Steady State | R _{thJF} | 17 | 21 | | |

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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| SPECIFICATIONS T _J = 25 °C, unless otherwise noted | | | | | | | |
|--|---------------------|---|-----|-------|-------|------|--|
| Parameter | Symbol | ol Test Conditions | | Тур. | Max. | Unit | |
| Static | | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$ | 2.0 | | 4 | V | |
| Gate-Body Leakage | I _{GSS} | $V_{DS} = 0 V, V_{GS} = \pm 20 V$ | | | ± 100 | nA | |
| | 1 | V _{DS} = 200 V, V _{GS} = 0 V | | | 1 | | |
| Zero Gate Voltage Drain Current | IDSS | V_{DS} = 200 V, V_{GS} = 0 V, T_{J} = 55 °C | | | 5 | μΑ | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \ge 5$ V, $V_{GS} = 10$ V | 8 | | | А | |
| | Б | V _{GS} = 10 V, I _D = 2.2 A | | 0.195 | 0.240 | 0 | |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = 6.0 V, I _D = 2.1 A | | 0.210 | 0.260 | Ω | |
| Forward Transconductance ^a | 9 _{fs} | V _{DS} = 15 V, I _D = 2.2 A | | 8.0 | | S | |
| Diode Forward Voltage ^a | V _{SD} | I _S = 2.1 A, V _{GS} = 0 V | | 0.8 | 1.2 | V | |
| Dynamic ^b | | | | | | | |
| Total Gate Charge | Qg | | | 12 | 18 | | |
| Gate-Source Charge | Q _{gs} | $V_{DS} = 100 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 2.2 \text{ A}$ | | 2.5 | | nC | |
| Gate-Drain Charge | Q _{gd} | | | 3.8 | | 1 | |
| Gate Resistance | Rg | | | 2.5 | | Ω | |
| Turn-On Delay Time | t _{d(on)} | | | 10 | 15 | | |
| Rise Time | t _r | V_{DD} = 100 V, R_L = 100 Ω | | 12 | 20 | | |
| Turn-Off Delay Time | t _{d(off)} | $\text{I}_\text{D}\cong \text{1}$ A, V_GEN = 10 V, R_g = 6 Ω | | 15 | 25 | ns | |
| Fall Time | t _f | | | 15 | 25 | | |
| Source-Drain Reverse Recovery Time | t _{rr} | I _F = 2.1 A, dl/dt = 100 A/µs | | 60 | 90 | | |

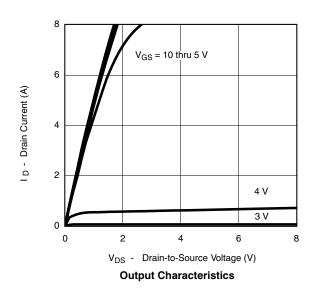
Notes:

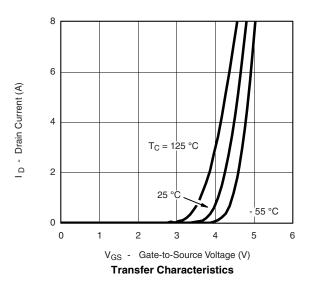
a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



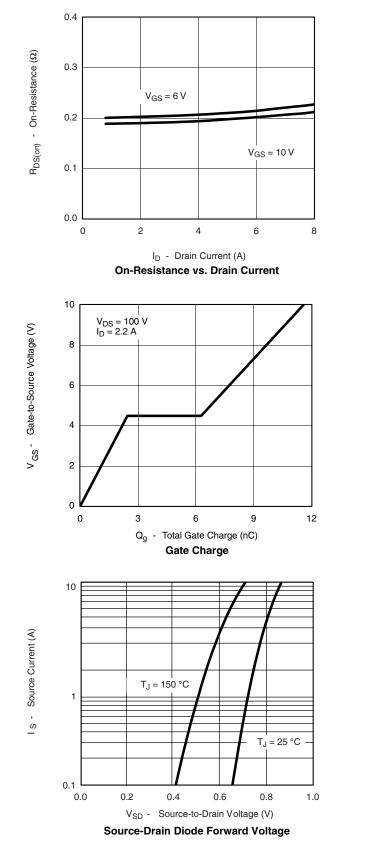


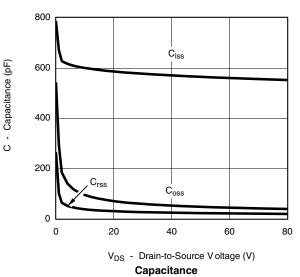


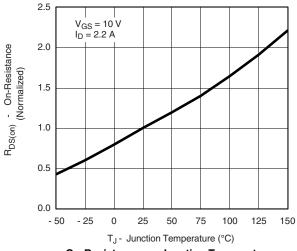
Si4464DY

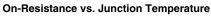
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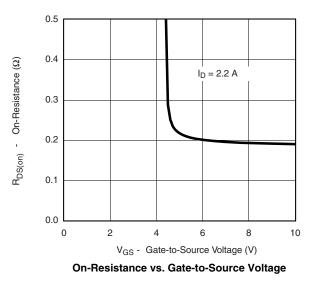
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted









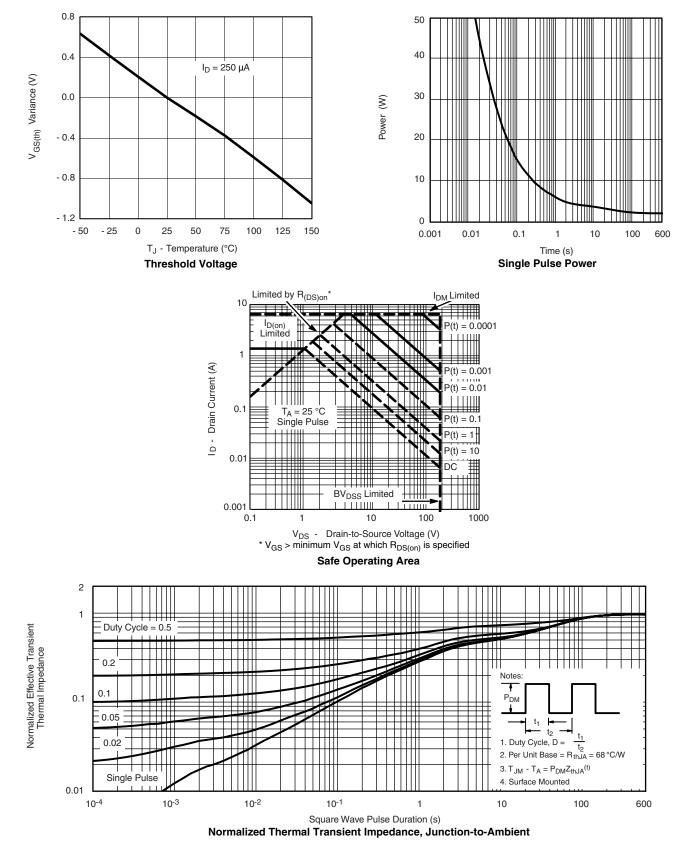


Document Number: 72051 S09-0705-Rev. C, 27-Apr-09

Si4464DY

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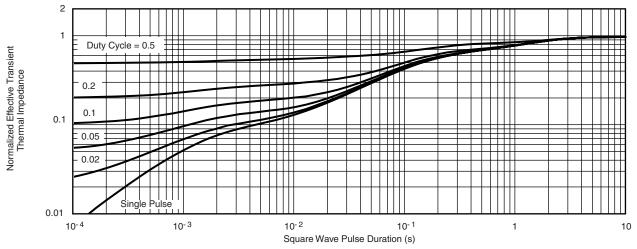






Si4464DY Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg772051.



Package Information

Vishay Siliconix

SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





| | MILLIM | IETERS | INCHES | | | |
|---|--------|--------|-----------|-------|--|--|
| DIM | Min | Мах | Min | Max | | |
| A | 1.35 | 1.75 | 0.053 | 0.069 | | |
| A ₁ | 0.10 | 0.20 | 0.004 | 0.008 | | |
| В | 0.35 | 0.51 | 0.014 | 0.020 | | |
| С | 0.19 | 0.25 | 0.0075 | 0.010 | | |
| D | 4.80 | 5.00 | 0.189 | 0.196 | | |
| E | 3.80 | 4.00 | 0.150 | 0.157 | | |
| е | 1.27 | BSC | 0.050 BSC | | | |
| н | 5.80 | 6.20 | 0.228 | 0.244 | | |
| h | 0.25 | 0.50 | 0.010 | 0.020 | | |
| L | 0.50 | 0.93 | 0.020 | 0.037 | | |
| q | 0° | 8° | 0° | 8° | | |
| S | 0.44 | 0.64 | 0.018 | 0.026 | | |
| ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498 | | | | | | |

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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